

END of STAVE THERMAL FEA

(Barrel Stave 130)

- o Aim is to estimate effect of EoS chip heat on -
 - *Sensor: Temperature, Runaway Headroom*
 - *EoS: GBT chipset, VECSL temperatures*

- o TWO Phases of Interest, with different coolant temperatures, T_c :
 - *Operation: $T_c \sim -30C$*
 - *Stave Integration: tracker above dew-point (not closed): $T_c \sim +15C$ (45C higher!)*

- o Assume (for now) a Conventional Stave Core: Side Mounted Cards top and bottom.
 - *Focus on feasibility of a simplified cooling pipe*

- o “Speculative” Many of the FEA ingredients are **uncertain!**

EoS COMPONENTS - THERMAL

VTR: Assume physically similar to SMU design (Dual Tx for Calo):

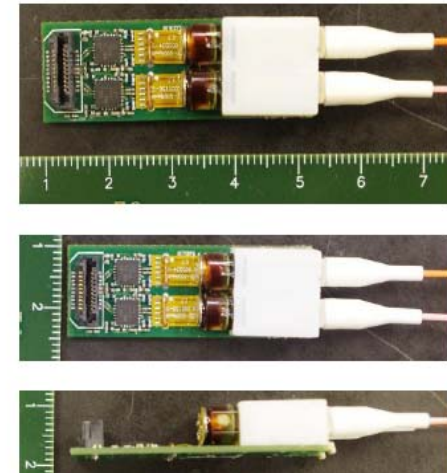
Transmitter: 217mW (LpGBLD 40% lower. Still in 130nm)

Receiver: 120mW (+ PIN diode ff. Rad.damage ?)

(? Jan Troska, AUW: "VTR doesn't need active cooling")

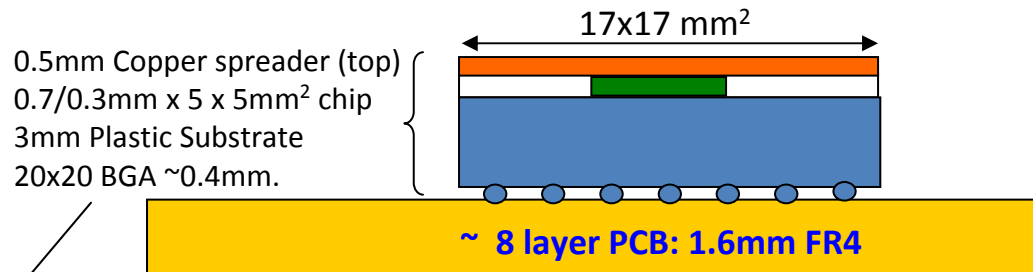
FEA: VTR NOT modelled thermally (only cosmetic)...

Inject VTR Heat into connector footprint.



GBT: 1.8W (Lp version - 65nm Schedule+Reliability issues.)

Package: ASE(Taiwan) via IMEC:



PCB:

Assume 2x17 μ m Cu planes
(! heat spreading near chip).

Thermal Vias: Not in FEA (needs design): could reduce ΔT by $\times 3$?

Not final package? Thermal R (die => board) not known (aim to measure!).

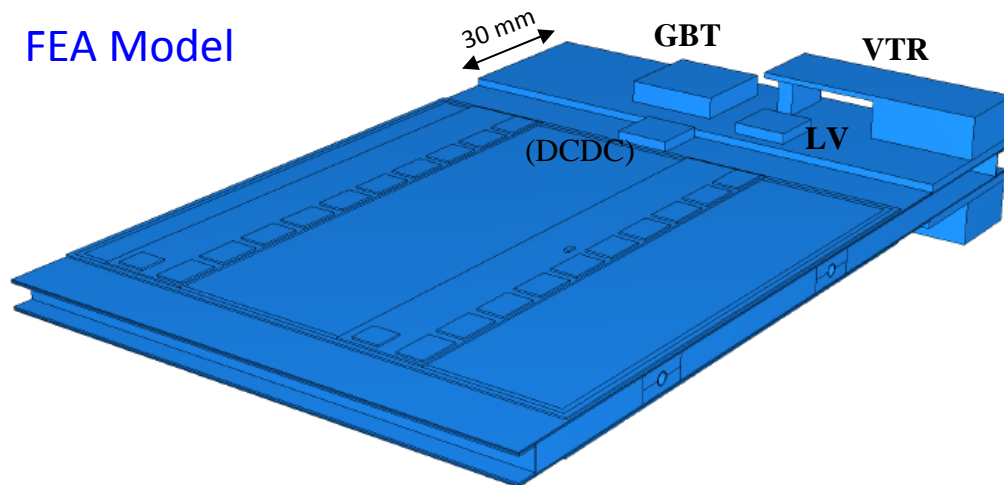
FEA: Assume 10C/W (experience with Motorola MCP7447A ceramic). Model as isotropic, $K = 1.4W/m-K$.

Power Conversion: Useful Power 2.14W

Assume (aggressive) 75% efficiency => **0.7 W (conversion)**

Total SMC power (per face) 2.84W (equiv.to $\sim \frac{1}{2}$ hybrid power)

FEA Model



Conduction to adjacent module is $\sim 20\%$: neglected here.

LV and VTR are cosmetic only, apart from heat injected into PCB footprint! GBT is modelled, to have some estimate of die temperature.

DESY meeting: wider PCB (50mm?)

(For convenience have suppressed honeycomb volumes: were modelled as air)

CO₂ Temperature (Boundary Conditions) – refinement of previous FEA!

Pressure drop \Rightarrow Temperature drop of $\sim 3\text{C}$ along pipe (will be measured at CERN).

- Mean fluid T is 1.5 degrees below input T. (\Rightarrow correction to Runaway Headroom: now "23C wrt input fluid")
- Fluid T vs Z: \sim equal at Z=0, increasingly asymmetric towards EoS.



\Rightarrow In presence of other sources of asymmetry, direction of flow matters!

NEAR End of Stave (but away from SMC): Temperature variation across Sensor.

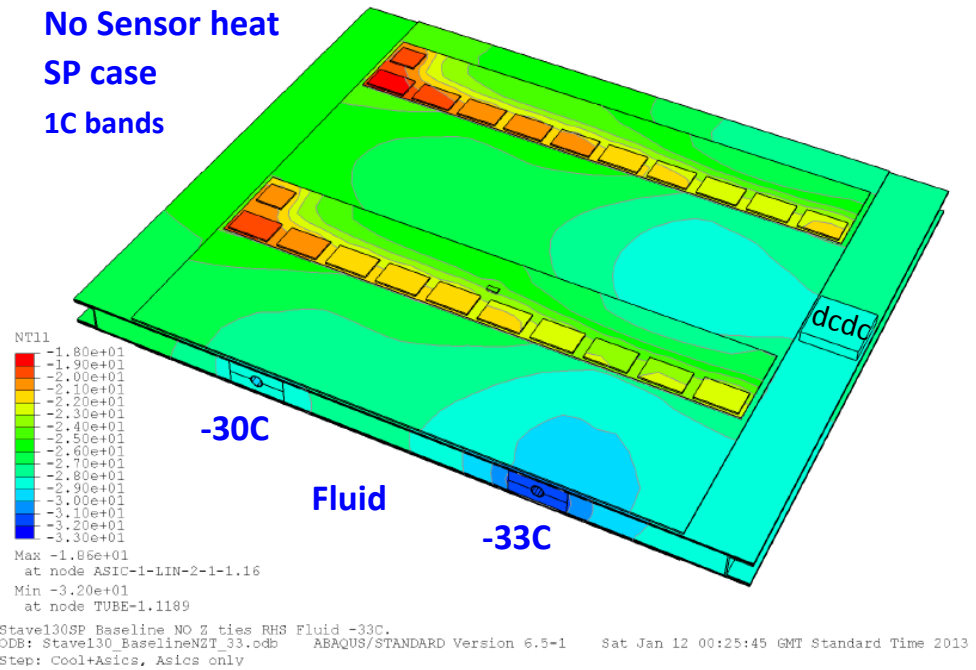
- No sensor heat (3000 fb^{-1} , -25C expect $\sim 0.4\text{W}$)
- Hybrid heat $5.6\text{W}/\text{module face}$ ($\sim 1\text{mW}/\text{chan}$).

Sensor T Variation due to:

- Hybrid/HCC/Pipe: 3.5C
- Asymmetric fluid T: 2C

gives for:

- SP: ~ 5.5 degrees over sensor area.
- DCDC (edge-mounted):
 - ~ 4 deg. (fluid as shown) Preferred?
 - ~ 7 deg. (flow reversed) Uncomfortable?



This perhaps sets the scale for acceptable level of T variation due to presence of SMC.

Note: The above FEA plot neglects heat flow between modules due to asymmetric hybrid placement.

Hybrid placement affects the range of T variation across the sensor: IF symmetrically placed hybrids have become the baseline it would be an advantage to change the model to reflect that!

Convection + Radiation - appreciable since the SMC and chips are at relatively high T.

- included crudely in the model as a surface film effect at the pcb surface (biggest contribution):

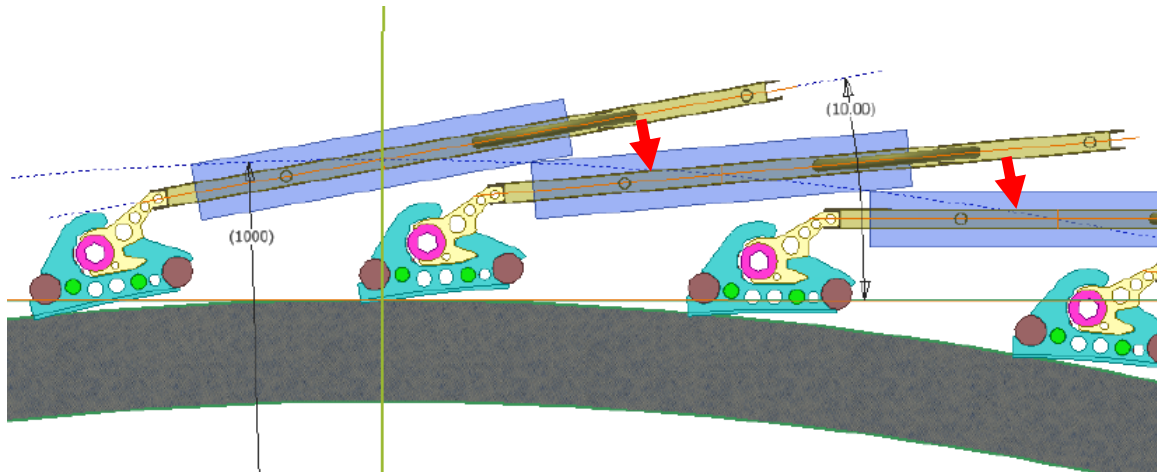
htc 10 W/m²K ; ambient T -23.5C (approx. mean stave surface T).

- accounts for about 0.4W (15%) heat *loss* from the SMC.

- lowers the GBT chip T by typically 5C.

Where does the heat go?

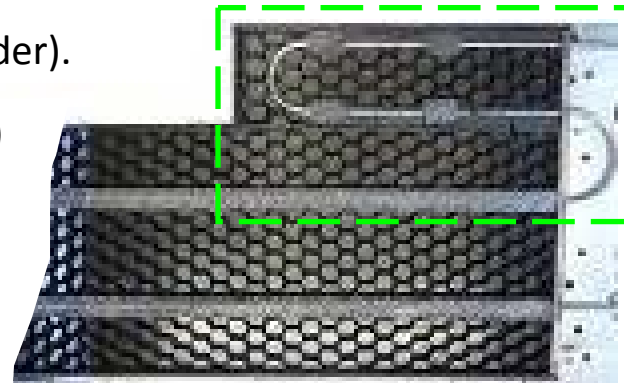
At worst, it is a 0.5W load on the module below (<10% hybrid heat) - *Ignored in the FEA.*



The Pipe “Wiggle” Issue:

To date, cooling pipe formed with a wiggle (meander).

- brings the coolant close to the SMC chips (good!)
- cools the sensor to below typical sensor T.



Several reasons to suppress / simplify this structure:

- Mechanical simplicity
- Avoid the loop outside stave end => close the gap between stave and barrel interlinks
- Reduce the Ti pipe length (avoids a weld?)
- **Operationally**: Avoid the associated pressure drop (note small radius bends) , *particularly* if located at *outlet* i.e. between the stave and the back pressure regulation.

=> Motivates cooling structure with straight pipes (or reduced meander) + passive conduction.

Result for Straight Pipes (no wiggle) – no additional conductive material in core.
! Fluid OUTlet (-33C) on SMC side.

Effect of SMC on the Sensor (SP case):

- T gradient (due to fluid) is reversed:
 => **nett T variation = 5.5C (i.e. no worse)!**
- Mean Sensor T raised by 1.9C, slightly lower R_T (SMC spreading?)

=> **Runaway Headroom reduced by 1.5C**
(23=>21.5 degrees)

CONCLUDE: With this direction of fluid flow, the effects of SMC heat on Runaway Headroom and nett Sensor T variation are small.

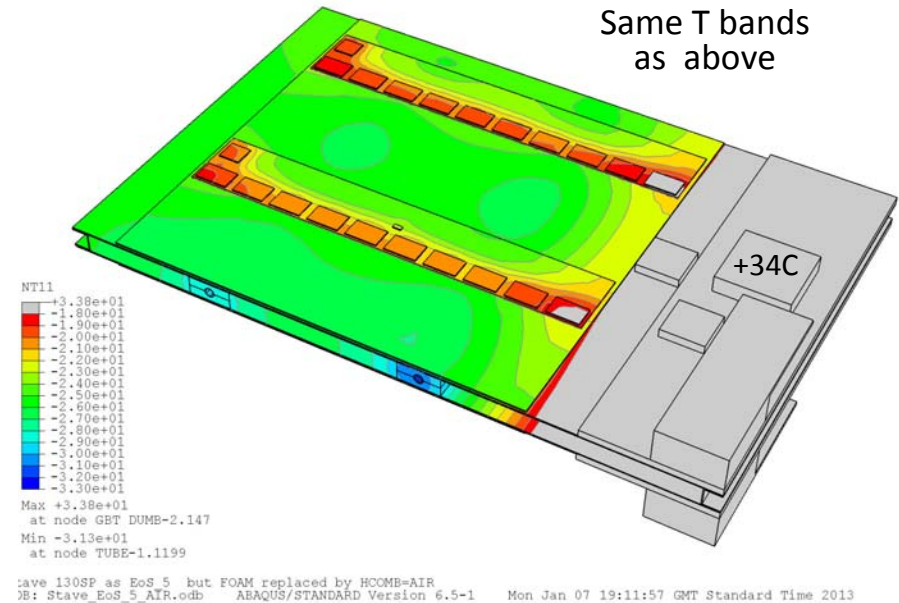
=> Forget about the runaway aspect!
(Additional material and intelligent channelling of the SMC heat can only improve this).

- looks a lot better than I said at the AUW: largely due to lower assumed SMC power and the fluid asymmetry.
(Berlin NH Hotel napkin: "Inspiration can hit you at any time"...))

In the analytic approximation to runaway: A change in headroom due to a fixed ΔQ that raises the Sensor temperature by ΔT (in absence of leakage current), is equivalent to changing the coolant temperature by the same ΔT . (...true so long as the Sensor T is fairly uniform).

(note $Q_{\text{hybrid}} \sim 6W$, $Q_{\text{SMC}} \sim 3W$).

However.....



=> GBT chip temperature in above configuration is high: **+34C** (! 67 degrees above fluid T).
 - Implies that during integration GBT sits at **+80C. (too high?)**.
 (Assuming pcb thermal vias, maybe +24C (opn.), +70C (intgn) - Still too high?).

FEA: run pipe directly under GBT => +11C => **Lateral heat xfer to straight pipe costs 23 degrees.**

Not enough Lateral conduction!

Compare: CFRP: 0-90-0 100gsm K13D2U, 140W/mK * 0.21mm => 30 [W.mm/mK]

...or, much worse (**need to measure!**): 45gsm K13C2U expect 10 ?

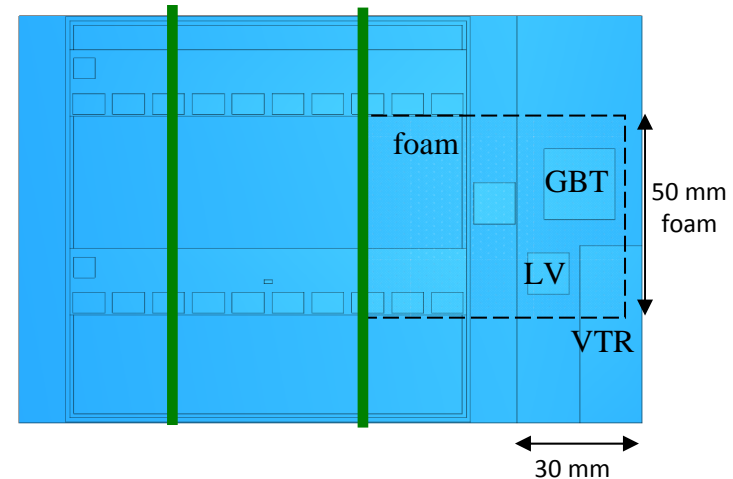
Try: Replace honeycomb by Allcomp Foam (ρ 0.25 g/cm³), 30W/mK * 2mm 60.

=> Add foam 56mm <X> x 50mm <Z> :GBT (+34C) => **+24C**

Extend to 98mm along Z => **+21C**

GBT now within 10 degrees of wiggle configuration.

Assuming pcb vias: +11C (operation) / +56C (integration)



Material Cost of Foam:

Foam 56 x 98 x 4mm total, $\rho = 0.25$, $X_0 = 43\text{g/cm}^2$: **0.13 cm²**

cf **Ti pipe wiggle**: 36cm x 2mm id x 0.14mm wall, $\rho = 4.51$, $X_0 = 16.2\text{ g/cm}^2$: **0.1 cm²**

SMC boards - !!FR4 ONLY 3 x 10 x 0.16 cm³, $X_0 = 16.8\text{cm}$: **0.6 cm²**

- conclude no need to worry about foam inserts (use more if helps?).

Additional Strategy: Divert the Cooling Pipe towards the SMC –

Somehow shape pipe (e.g. zig-zag to reduce distance to SMC? Tricky. . .

e.g. Shift pipe 20mm towards SMC => **Further cools GBT by 3C.**

BUT: Knocks 4C off Runaway Headroom!

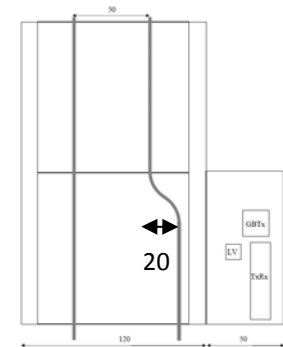
WHY?

- STAVE Cooling philosophy is to distribute the cooling pipes evenly across the sensor. . .

Disturbing this increases thermal resistance R_T (Sensor Heat => Coolant) (above: by 16%).

(A change in R that increases the sensor T (in absence of leakage current) by ΔT reduces the headroom by $\sim 3x\Delta T$. Changing R is 3x as dangerous as changing Q , cf straight pipe result).

- *Introducing a small meander into the pipe to help cool the SMC (or for other reasons) can seriously harm the runaway headroom: could be done but would involve some TLC and yet more foam*



Summary

- In absence of the Wiggle”, ~3W EoS(SMC) heat will not seriously degrade runaway performance – at least if the fluid outlet (lower temperature) is on the same side of the stave.
- GBT chip T: Nothing is quite as effective as wiggling the cooling pipe to pass under the chip.but inserting 30W/mK foam into the core can approach it to within ~ 10 degrees . . .(+11/+56C)
Acceptable? - depends on what is an acceptable chip temperature (assuming model OK!).

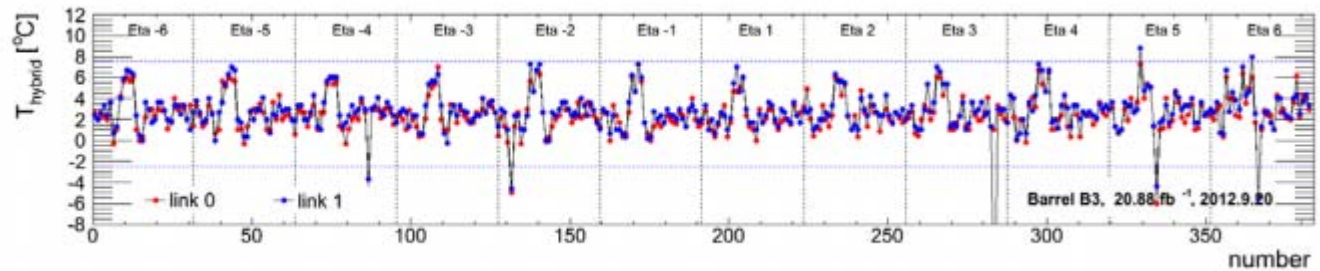
It would be helpful to understand better:

- (trivially) how the hybrids will be placed along Z (symmetrically or not).
- dimensions the SMC card – (problem if chips too far from pipe!).
- what PCB thermal vias are possible.
- packaging / thermal paths of the EoS chips (GBT, GBTLD, GBTLIA, VECSL)
- how efficiently the LV conversion can be done.
- What are the acceptable T ranges for EoS chips: during operation? during integration? (lifetime/reliability issue !).

BACKUP:

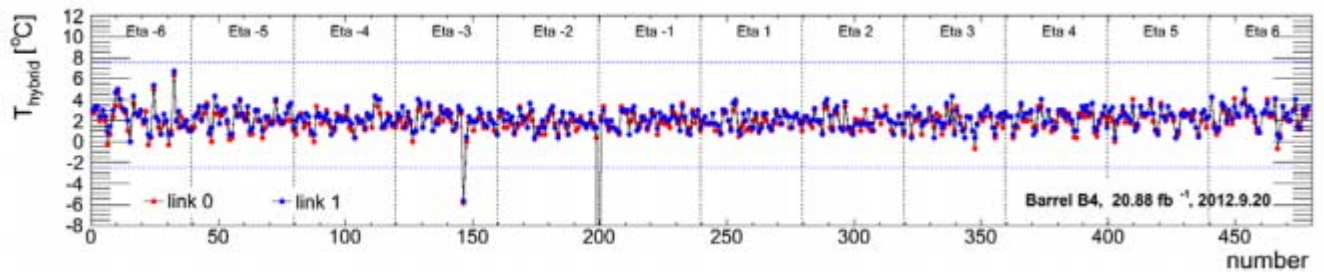
Plots from Steve McMahon of Current SCT temperature:

T_{hybrid}



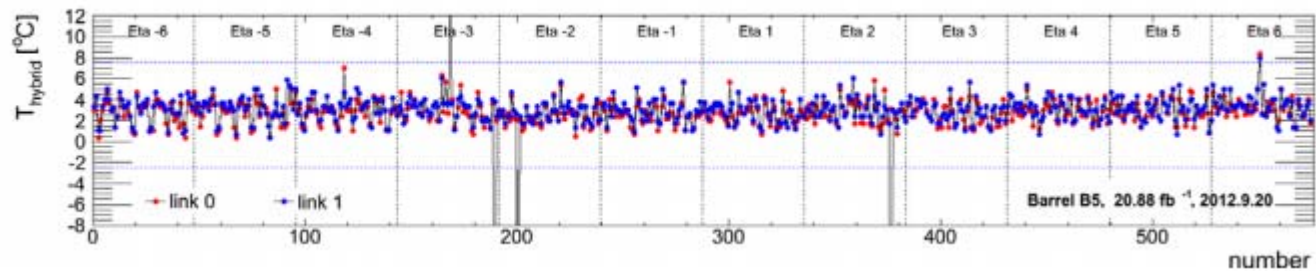
number

T_{hybrid}



number

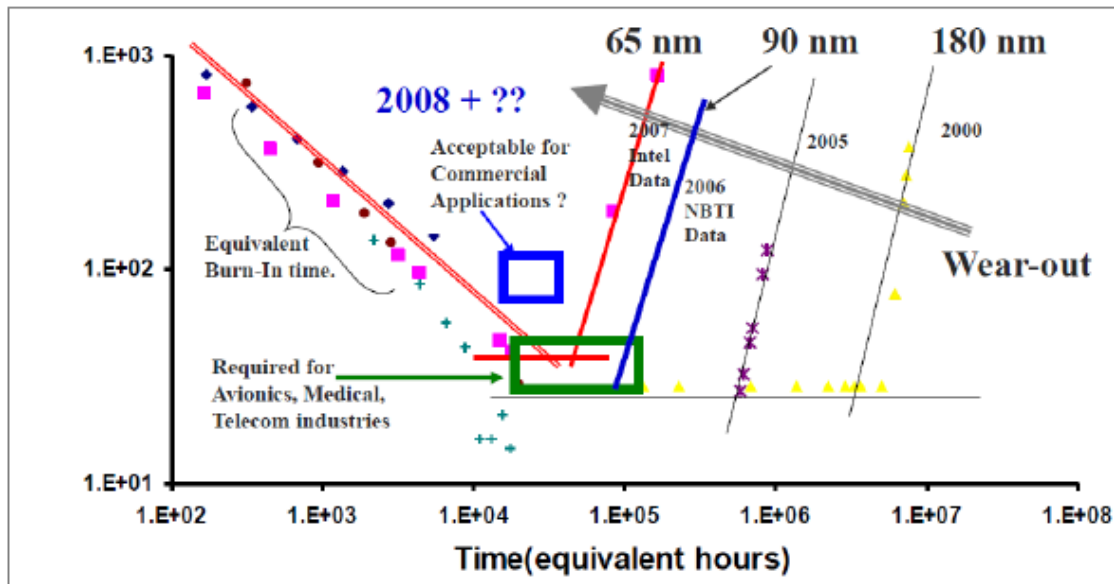
T_{hybrid}



number

FA Webinar- Cheryl Tulkoff

Failure Rates and The Bathtub Curve



- Field data shows that each new generation of integrated circuits is beginning to wearout sooner than the last
 - Typically misconstrued as pre-mature wearout

DfR Solutions